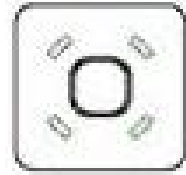


Wafer Information

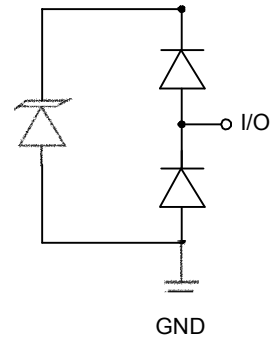
Item	Description
Wafer Size	6 inch (150mm)
Wafer Thickness	150um ± 10um
Die Size (with scribe lane)	206um x 206um
Bond Pad Opening	72um x 72um
Scribe Lane Width	50um
Gross Die Per Wafer	357,000
Top Metal (for wire bond)	AlSiCu 4um
Backside Metal (for die bond)	TiNiAgSn 1/3/5/14KÅ

- Complies with IEC 61000-4-2 standards:
Contact discharge: ±20kV

Die Appearance



Circuit Diagram



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	56	W
Peak Pulse Current (8/20μs)	IPP	4	A
Operating Temperature Range	T_J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	
Breakdown Voltage	VBR	4.2			V	$I_T = 1\text{mA}$
Reverse Leakage Current	IR			100	nA	VRWM = 3.3V
Forward voltage	VF			1.2	V	$I_F = 15\text{mA}$
Clamping Voltage	VC			10	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	VC			14	V	IPP = 4A (8 x 20μs pulse)
Junction Capacitance	C_J		0.45	0.60	pF	VR = 0V, f = 1MHz

Note: Electrical parameters are only for die, performance may alter after assembly.

NOTICE

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